

# DEVELOPMENT SAMPLE DATA

This information is derived from development samples made available for evaluation. It does not necessarily imply that the device will go into regular production.

SBB2632P SBB2632D  
SBB2632E

## 32 768 BIT STATIC READ ONLY MEMORY

The SBB2632 is a 32 768 bit MOS N-channel static Read Only Memory. It is organised as 4096 eight-bit words.

This ROM is designed for memory applications where high performance, large bit storage, and simple interfacing are important design objectives.

### QUICK REFERENCE DATA

|                               |           |      |         |    |
|-------------------------------|-----------|------|---------|----|
| Supply voltage                | $V_{DD}$  | nom. | 5       | V  |
| Supply current                | $I_{DD}$  | max. | 80      | mA |
| Operating ambient temperature | $T_{amb}$ |      | 0 to 70 | °C |

### PACKAGE OUTLINE

24-lead dual in line Plastic (SOT-101): SBB2632P, Cerdip (SOT-94): SBB2632D  
Cerdil (SOT-88): SBB2632E

### BLOCK DIAGRAM

purple binder, tab 7

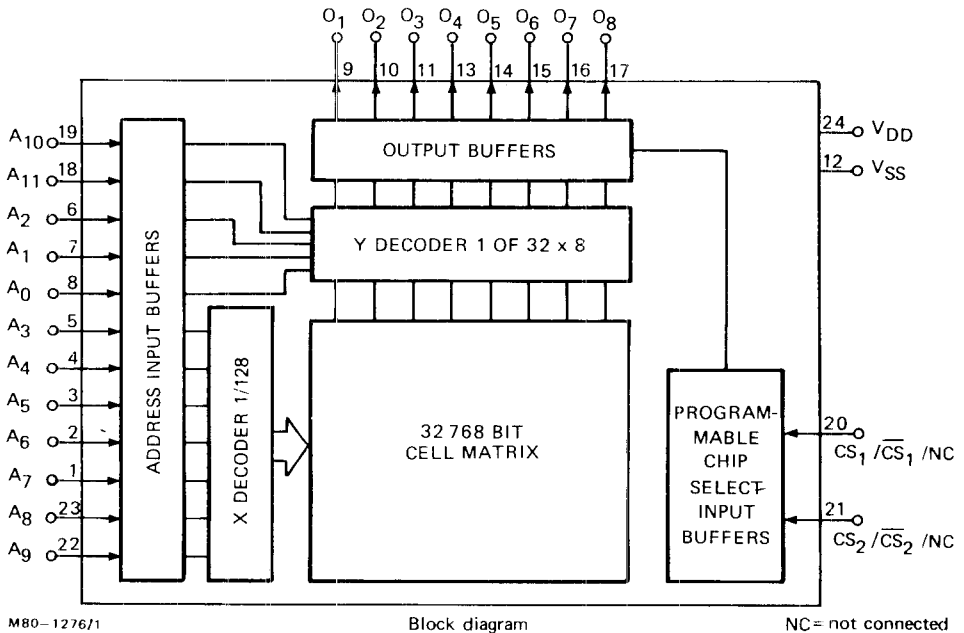


Fig.1



**Mullard**

November 1980

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## 32 768-BIT STATIC READ ONLY MEMORY

The SBB2632 is a 32 768 bit MOS N-channel static ROM organised as 4096 eight-bit words. This ROM is designed for memory applications where high performance, large bit storage, and simple interfacing are important design considerations.

### Features

- 450 ns access time; 2 TTL loads
- Two programmable chip select inputs
- Fully decoded
- All inputs and outputs directly TTL compatible
- Three-state outputs; OR-tied capability
- Single +5 V ± 10% power supply
- Protected inputs

### QUICK REFERENCE DATA

|                                     |                  |      |          |    |
|-------------------------------------|------------------|------|----------|----|
| Supply voltage                      | V <sub>DD</sub>  | nom. | 5        | V  |
| Supply current                      | I <sub>DD</sub>  | max  | 80       | mA |
| Operating ambient temperature range | T <sub>amb</sub> |      | 0 to +70 | °C |

purple binder, tab 5

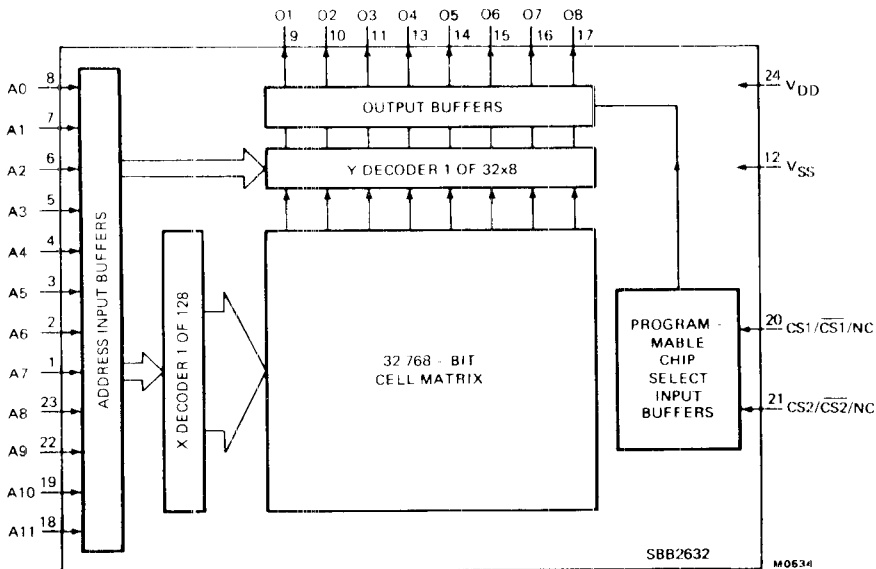


Fig. 1 Block diagram

### PACKAGE OUTLINES

SBB2632P: 24-lead DIL; plastic (SOT-101A)

SBB2632D: 24-lead DIL; ceramic (SOT-94)

SBB2632E: 24-lead DIL; metal-ceramic (SOT-86B)



**Mullard**

December 1982

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PINNING

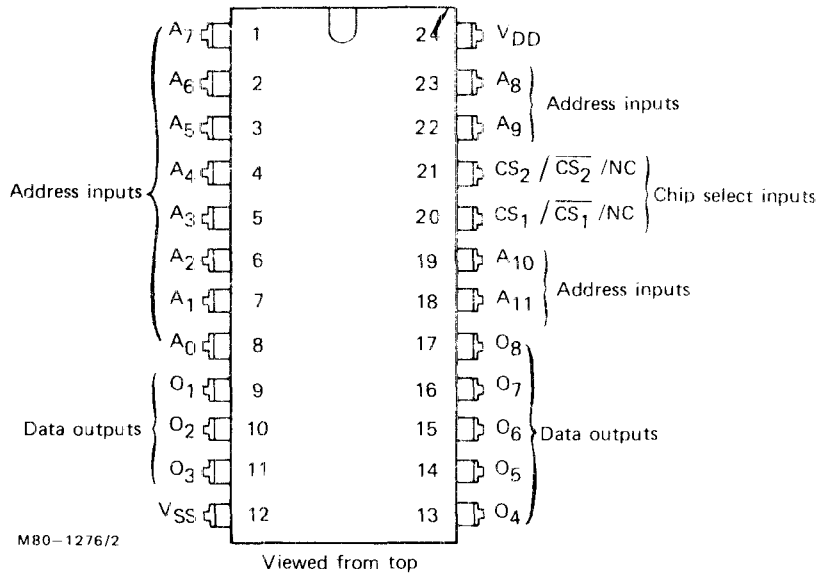


Fig.2

**DESCRIPTION**

The SBB2632 is a mask-programmable ROM and is manufactured to contain customer-defined data. The two chip select inputs are also programmable and any combination of active high or low or not connected chip select inputs can be defined by the customer. This combined with the 3-state data outputs allows the circuits to be 'OR TIED' for direct memory expansion.

The circuit requires a 5 V power supply and all inputs and outputs are directly TTL compatible.

**HANDLING**

Inputs and outputs are protected against electrostatic charge in normal handling. However, to be totally safe, it is desirable to take normal precautions appropriate to handling MOS devices (See MOS Handling Notes).



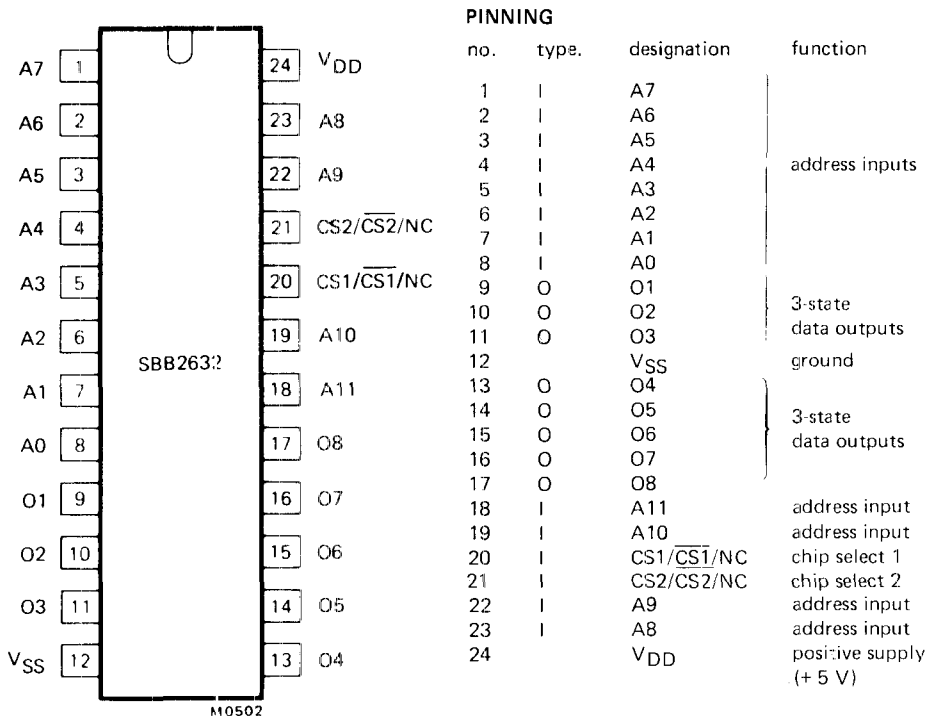


Fig.2 Pinning diagram.

**GENERAL DESCRIPTION**

The SBB2632 is a mask-programmable ROM and is manufactured to contain customer-defined data. The two chip select inputs are also programmable, and any combination of active HIGH or LOW level or not connected chip select inputs can be defined by the customer. This, combined with the 3-state data outputs, allows the circuits to be 'OR TIED' for direct memory expansion. The circuit requires a single +5 V power supply, and all inputs and outputs are directly TTL compatible.

**HANDLING**

Inputs are protected against electrostatic charge in normal handling. However, to be totally safe, it is desirable to take precautions appropriate to handling MOS devices (See 'Handling MOS Devices').



## RATINGS

Limiting values in accordance with the Absolute Maximum System

## Voltages (with respect to pin 12)

|   |          | min. | max. |   |
|---|----------|------|------|---|
| Supply voltage (pin 24)                                     | $V_{DD}$ | -0.5 | 7.0  | V |
| Input voltage - All inputs<br>(pins 1 to 8 and 18 to 23)    |          | -0.5 | 7.0  | V |
| Output voltage - All outputs<br>(pins 9 to 11 and 13 to 17) |          | -0.5 | 7.0  | V |

## Temperatures

|                       |           |            |    |
|-----------------------|-----------|------------|----|
| Storage temperature   | $T_{stg}$ | -65 to 150 | °C |
| Operating temperature | $T_{amb}$ | 0 to 70    | °C |

## CHARACTERISTICS

| Supply voltage    | min. | typ. | max. |   |
|-------------------|------|------|------|---|
| $V_{DD}$ (pin 24) | 4.75 | 5.0  | 5.25 | V |

The following characteristics apply at  $T_{amb} = 0$  to 70 °C and  $V_{DD} = 5.0$  V + 5% unless otherwise stated.

## Supply current

|   |   |   |    |    |
|---|---|---|----|----|
| $I_{DD}$ ( $T_{amb} = 25$ °C, outputs unloaded, $V_{in} = V_{DD}$ ) | - | - | 80 | mA |
|---|---|---|----|----|

## All Inputs (pins 1 to 8 and 18 to 23)

|   |          |     |   |          |    |
|---|----------|-----|---|----------|----|
| Input voltage; HIGH                                   | $V_{IH}$ | 2.0 | - | $V_{DD}$ | V  |
| Input voltage; LOW                                    | $V_{IL}$ | 0   | - | 0.8      | V  |
| Input load current ( $V_{in} = 0$ to 5.25 V)          | $I_{IN}$ | -   | - | 10       | µA |
| Input capacitance ( $T_{amb} = 25$ °C, $f = 1.0$ MHz) |          | -   | - | 7        | pF |

## All outputs (pins 9 to 11 and 13 to 17)

|   |          |     |   |          |    |
|---|----------|-----|---|----------|----|
| Output voltage; HIGH ( $I_{OH} = -100$ µA)  | $V_{OH}$ | 2.4 | - | $V_{CC}$ | V  |
| Output voltage; LOW ( $I_{OL} = 1.6$ mA)  | $V_{OL}$ | -   | - | 0.4      | V  |
| Output current in high impedance state<br>(chip de-selected $V_{out} = 0.4$ V to $V_{DD}$ ) |          | -   | - | 10       | µA |
| Output capacitance ( $T_{amb} = 25$ °C, $f = 1.0$ MHz)                                      |          | -   | - | 10       | pF |

DEVELOPMENT SAMPLE DATA



**RATINGS** ( $V_{SS} = 0$  V)

Limiting values in accordance with the Absolute Maximum System (IEC 134)

|                                     |           |      |             |    |
|-------------------------------------|-----------|------|-------------|----|
| Supply voltage                      | $V_{DD}$  | max. | 7           | V  |
| Input voltage                       | $V_I$     | max. | 7           | V  |
| Output voltage                      | $V_O$     | max. | 7           | V  |
| Total power dissipation per package | $P_{tot}$ | max. | 1           | W  |
| Operating ambient temperature range | $T_{amb}$ |      | 0 to +70    | °C |
| Storage temperature range           | $T_{stg}$ |      | -65 to +150 | °C |

**D.C. CHARACTERISTICS** $V_{SS} = 0$  V;  $V_{DD} = 4.5$  to  $5.5$  V;  $T_{amb} = 0$  to  $+70$  °C; unless otherwise stated.

DEVELOPMENT SAMPLE DATA

| parameter                              | symbol   | min. | typ. | max.       | conditions  |
|--|----------|------|------|------------|---|
| Supply voltage                         | $V_{DD}$ | 4.5  | 5.0  | 5.5 V      |   |
| Supply current                         | $I_{DD}$ | —    | —    | 80 mA      | chip deselected<br>$V_{DD} = 5.5$ V<br>$V_I = V_{DD}$ |
| <b>Inputs</b>                          |          |      |      |            |   |
| Input voltage; HIGH                    | $V_{IH}$ | 2.0  | —    | $V_{DD}$ V |   |
| Input voltage; LOW                     | $V_{IL}$ | 0    | —    | 0.8 V      |   |
| Input load current                     | $I_I$    | —    | —    | 10 $\mu$ A | $V_I = 0$ to 5.5 V<br>$V_{DD} = 5.5$ V                |
| Input capacitance                      | $C_I$    | —    | —    | 7 pF       | $f = 1$ MHz;<br>$T_{amb} = 25$ °C                     |
| <b>Outputs</b>                         |          |      |      |            |   |
| Output voltage; HIGH                   | $V_{OH}$ | 2.4  | —    | $V_{DD}$ V | $-I_{OH} = 200$ $\mu$ A                               |
| Output voltage; LOW                    | $V_{OL}$ | —    | —    | 0.4 V      | $I_{OL} = 3.2$ mA, $V_{DD} = 4.5$ V                   |
| Output current in high-impedance state | $I_O$    | —    | —    | 10 $\mu$ A | chip deselected<br>$V_O = 0.4$ V to $V_{DD}$          |
| Output capacitance                     | $C_O$    | —    | —    | 10 pF      | $f = 1$ MHz;<br>$T_{amb} = 25$ °C                     |



**A.C. CHARACTERISTICS**

$V_{SS} = 0\text{ V}$ ;  $V_{DD} = 5\text{ V} \pm 10\%$ ;  $T_{amb} = 0\text{ to }+70\text{ }^{\circ}\text{C}$  unless otherwise specified.  
 Input transition time = 20 ns

|  | symbol    | min. | typ. | max.   | conditions                            |
|--|-----------|------|------|--------|---------------------------------------|
| <b>Timings (note 1; Fig.3)</b>                 |           |      |      |        |                                       |
| Address access time                            | $t_{ACC}$ | —    | —    | 450 ns | Output load is 2 TTL loads and 100 pF |
| Chip select delay (note 2)                     | $t_{CO}$  | —    | —    | 150 ns |                                       |
| Chip de-select delay (note 3)                  | $t_{DF}$  | —    | —    | 100ns  |                                       |
| Previous data valid after address change delay | $t_{OH}$  | 20   | —    | — ns   |                                       |

**Notes**

1. Timing reference levels: inputs = 1.5 V.  
 outputs = 0.6 V and 2.2 V.
2. This maximum value of  $t_{CO}$  applies providing the valid address leads the chip select by  $(t_{ACC} - t_{CO})$ ns or more.
3. Measured at  $V_{OL} = 0.8\text{ V}$  on the LOW to 3-state transition.

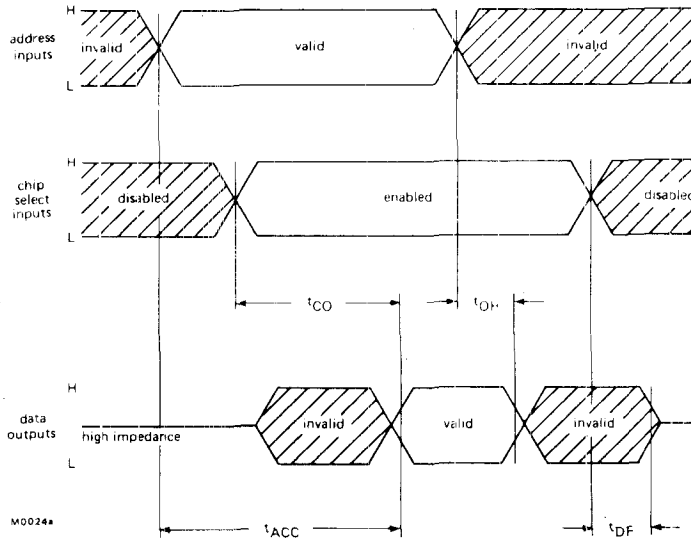


Fig.3 Timing diagram



**Timings**

|  |           | min. | typ. | max. |    |
|--|-----------|------|------|------|----|
| Address access time                            | $t_{ACC}$ | —    | —    | 450  | ns |
| Chip select delay                              | $t_{CO}$  | —    | —    | 200  | ns |
| Chip de select delay                           | $t_{DF}$  | —    | —    | 200  | ns |
| Previous data valid after address change delay | $t_{OH}$  | 20   | —    | —    | ns |

**TIMING DIAGRAM**

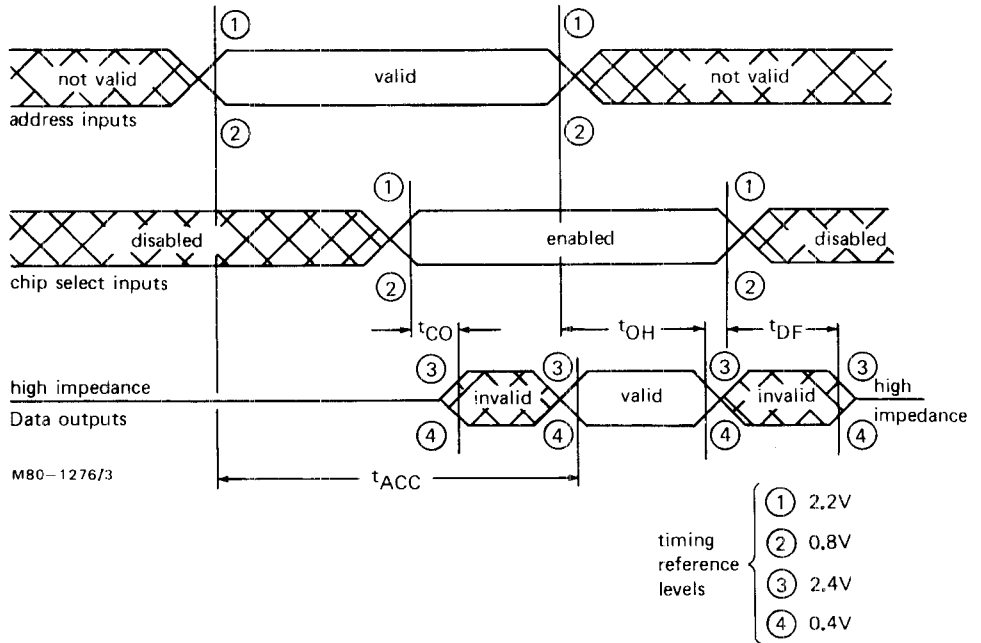
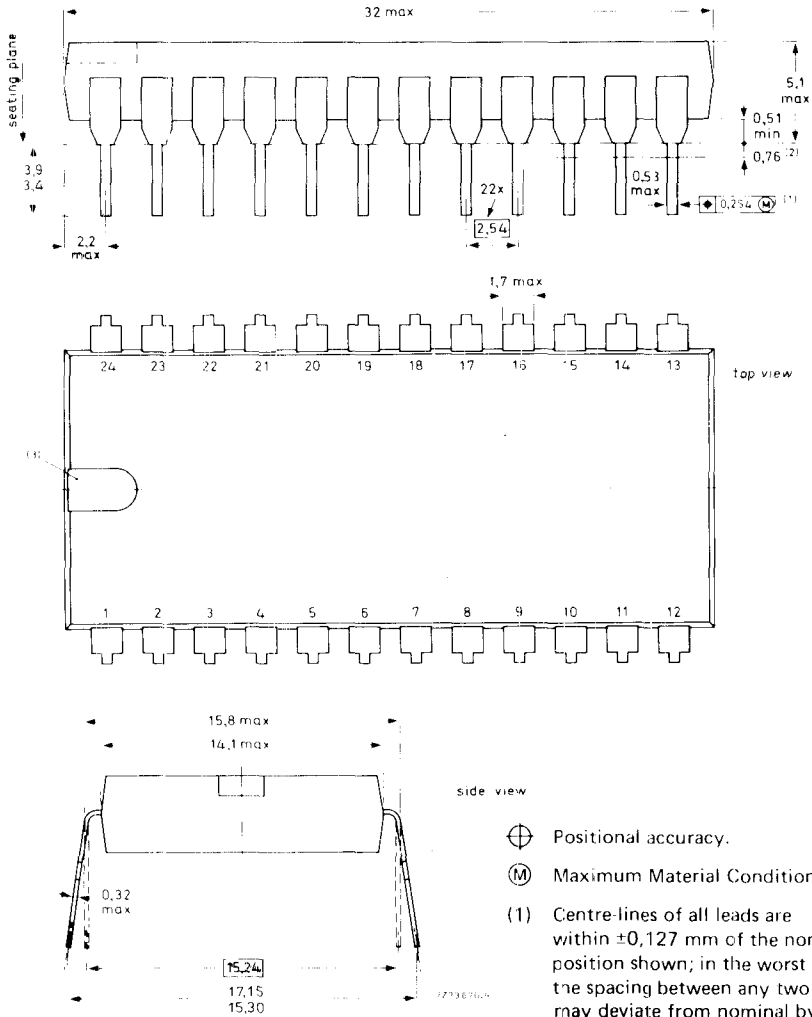


Fig.3



24-LEAD DUAL IN-LINE; PLASTIC (SOT-101A)



Dimensions in mm

- ⊕ Positional accuracy.
  - Ⓜ Maximum Material Condition.
- (1) Centre-lines of all leads are within  $\pm 0,127$  mm of the nominal position shown; in the worst case, the spacing between any two leads may deviate from nominal by  $\pm 0,254$  mm.
  - (2) Lead spacing tolerances apply from seating plane to the line indicated.
  - (3) Index may be horizontal as shown, or vertical.

SOLDERING

See next page



## SOLDERING

### 1. By hand

Apply the soldering iron below the seating plane (or not more than 2 mm above it).

If its temperature is below 300 °C it must not be in contact for more than 10 seconds; if between 300 °C and 400 °C, for not more than 5 seconds.

### 2. By dip or wave

The maximum permissible temperature of the solder is 260 °C; this temperature must not be in contact with the joint for more than 5 seconds. The total contact time of successive solder waves must not exceed 5 seconds.

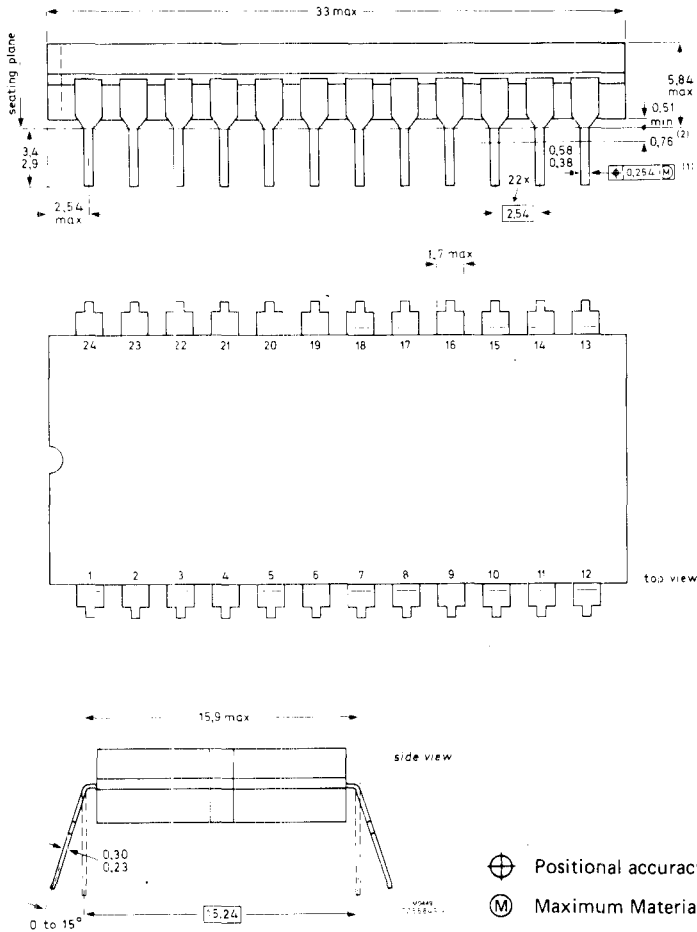
The device may be mounted up to the seating plane, but the temperature of the plastic body must not exceed the specified storage maximum. If the printed-circuit board has been pre-heated, forced cooling may be necessary immediately after soldering to keep the temperature within the permissible limit.

### 3. Repairing soldered joints

The same precautions and limits apply as in (1) above.



24-LEAD DUAL IN-LINE; CERAMIC (SOT-94)



1. Leads are given positive misalignment so that they grip after insertion.
2. Leads are Ni-Fe, pure tin plated.

- ⊕ Positional accuracy.  
 ⊕ Maximum Material Condition.
- (1) Centre-lines of all leads are within  $\pm 0,127$  mm of the nominal position shown; in the worst case, the spacing between any two leads may deviate from nominal by  $\pm 0,254$  mm.
  - (2) Lead spacing tolerances apply from seating plane to the line indicated.



